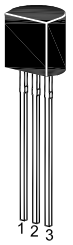
MPSH17

NPN Silicon Epitaxial Planar Transistor

The transistor is subdivided into one group according to its DC current gain.

On special request, these transistors can be manufactured in different pin configurations.



1. Emitter 2. Base 3. Collector
TO-92 Plastic Package

Absolute Maximum Ratings (T_a = 25 °C)

Parameter	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	20	V
Collector-Emitter Voltage	V_{CEO}	15	V
Emitter-Base Voltage	V_{EBO}	3	V
Collector Current	I_C	50	mA
Power Dissipation	P_{tot}	350	mW
Junction Temperature	T_j	150	°C
Storage Temperature Range	T_{stg}	- 55 to + 150	°C

Characteristics at T_a = 25 °C

Parameter	Symbol	Min.	Max.	Unit
DC Current Gain at I_C = 5 mA, V_{CE} = 10 V	h_{FE}	25	250	-
Collector Base Cutoff Current at V_{CB} = 15 V	I_{CBO}	-	100	nA
Collector Base Breakdown Voltage at I_C = 100 µA	$V_{(BR)CBO}$	20	-	V
Collector Emitter Breakdown Voltage at I_C = 1 mA	$V_{(BR)CEO}$	15	-	V
Emitter Base Breakdown Voltage at I_E = 10 µA	$V_{(BR)EBO}$	3	-	V
Collector Emitter Saturation Voltage at I_C = 10 mA, I_B = 1 mA	$V_{CE(sat)}$	-	0.5	V
Current Gain Bandwidth Product at I_C = 5 mA, V_{CE} = 10 V, f = 100 MHz	f_T	800	-	MHz
Collector Output Capacitance at V_{CB} = 10 V, f = 1 MHz	C_{ob}	0.3	0.9	pF